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30V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY $V_{(BR)DSS}$ =30V; $R_{DS(ON)}$ =0.22 Ω ; I_D =1.4A

DESCRIPTION

This new generation of high density MOSFETs from Zetex utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT23 package

APPLICATIONS

- DC DC Converters
- Power Management Functions
- Disconnect switches
- Motor control

ORDERING INFORMATION

DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXM61N03FTA	7	8mm embossed	3000 units
ZXM61N03FTC	13	8mm embossed	10000 units

S



Top View

DEVICE MARKING

N03







SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DSS}	30	V
Gate Source Voltage	V _{GS}	±20	V
Continuous Drain Current (V_{GS} =10V; T_A =25°C)(b) (V_{GS} =10V; T_A =70°C)(b)	I _D	1.4 1.1	А
Pulsed Drain Current (c)	I _{DM}	7.3	А
Continuous Source Current (Body Diode) (b)	I _S	0.8	А
Pulsed Source Current (Body Diode)	I _{SM}	7.3	А
Power Dissipation at T _A =25°C (a) Linear Derating Factor	P _D	625 5	mW mW/°C
Power Dissipation at T _A =25°C (b) Linear Derating Factor	P _D	806 6.4	mW mW/°C
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	R _{0JA}	200	°C/W
Junction to Ambient (b)	R _{0JA}	155	°C/W

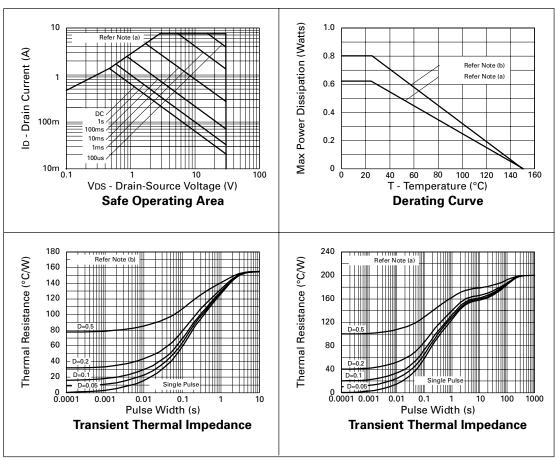
NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at t \leq 5 secs.

(c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.





CHARACTERISTICS



ELECTRICAL CHARACTERISTICS (at TA = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.(3)	MAX.	UNIT	CONDITIONS.	
STATIC			•				
Drain-Source Breakdown Voltage	V _{(BR)DSS}	30			V	I_{D} =250 μ A, V_{GS} =0V	
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} =30V, V _{GS} =0V	
Gate-Body Leakage	I _{GSS}			100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$	
Gate-Source Threshold Voltage	V _{GS(th)}	1.0			V	$I_D = 250 \mu A$, $V_{DS} = V_{GS}$	
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.22 0.30	Ω Ω	V _{GS} =10V, I _D =0.91A V _{GS} =4.5V, I _D =0.46A	
Forward Transconductance (3)	g _{fs}	0.87			s	V _{DS} =10V,I _D =0.46A	
DYNAMIC (3)						•	
Input Capacitance	C _{iss}		150		pF	V _{DS} =25 V, V _{GS} =0V, f=1MHz	
Output Capacitance	C _{oss}		35		pF		
Reverse Transfer Capacitance	C _{rss}		15		pF		
SWITCHING(2) (3)							
Turn-On Delay Time	t _{d(on)}		1.9		ns	V_{DD} =15V, I _D =0.91A R _G =6.2 Ω , R _D =16 Ω (refer to test circuit)	
Rise Time	t _r		2.5		ns		
Turn-Off Delay Time	t _{d(off)}		5.8		ns		
Fall Time	t _f		3.0		ns		
Total Gate Charge	Qg			4.1	nC		
Gate-Source Charge	Q _{gs}			0.4	nC	V _{DS} =24V,V _{GS} =10V, I _D =0.91A	
Gate-Drain Charge	Q _{gd}			0.63	nC	(refer to test circuit)	
SOURCE-DRAIN DIODE		1		1		1	
Diode Forward Voltage (1)	V_{SD}			0.95	V	T _J =25°C, I _S =0.91A, V _{GS} =0V	
Reverse Recovery Time (3)	t _{rr}		11.0		ns	T _J =25°C, I _F =0.91A, di/dt= 100A/μs	
Reverse Recovery Charge (3)	Q _{rr}		3.5		nC		

NOTES

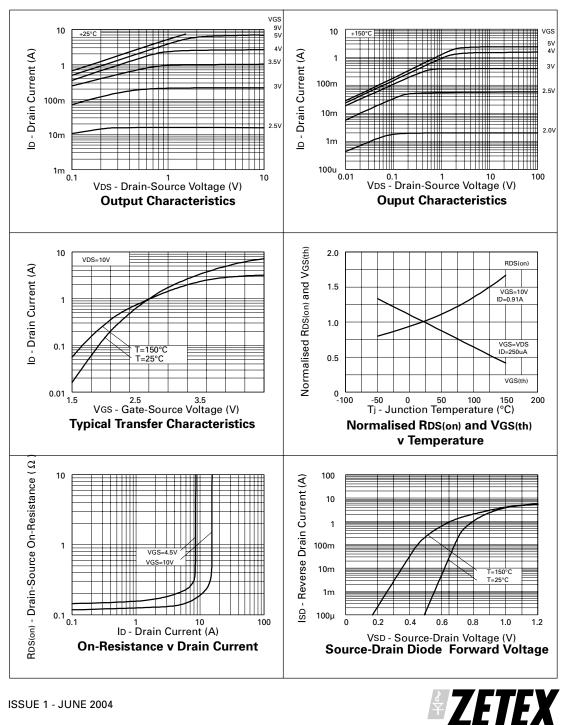
(1) Measured under pulsed conditions. Width≤300 $\mu s.$ Duty cycle ≤2% .

(2) Switching characteristics are independent of operating junction temperature.

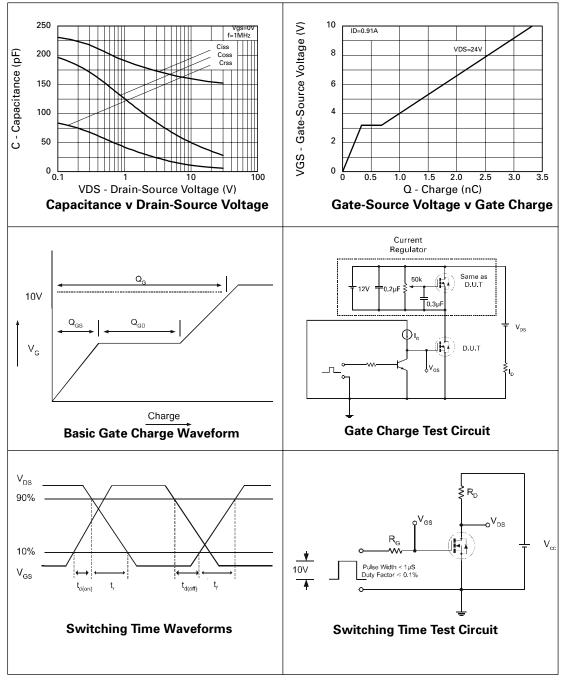
(3) For design aid only, not subject to production testing.







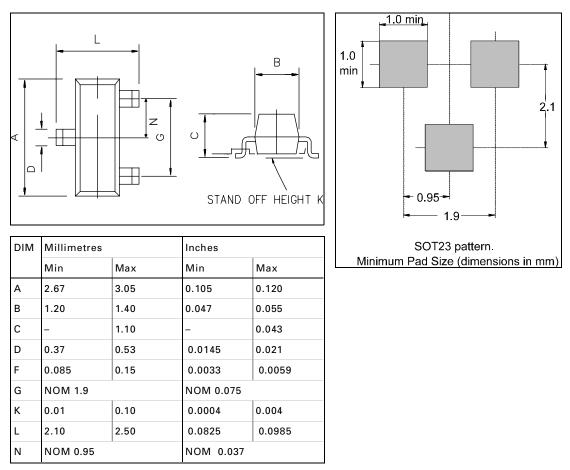
TYPICAL CHARACTERISTICS





PACKAGE DIMENSIONS

PAD LAYOUT DETAILS





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